





45V DUAL NPN SMALL SIGNAL TRANSISTOR

Features

- BV_{CEO} > 45V
- Low profile 0.4mm high package for thin applications
- Ultra-Small Surface Mount Package
- Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

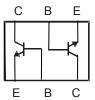
Mechanical Data

- Case: X2-DFN1310-6
- Nominal package height: 0.4mm
- Case Material: Molded Plastic, "Green" Molding Compound.
- UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu, Solderable per MIL-STD-202, Method 208 @4
- Weight: 0.0015 grams (approximate)

X2-DFN1310-6



Top View



Device Schematic Top View

Ordering Information (Note 4)

Part Number	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
BC847CDLP-7	1M	7	8	3000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http"//www.diodes.com/products/packages.html.

Marking Information

1M

1M = Product Type Marking Code

(Top View)



Maximum Ratings (@T_A = +25°C unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	50	V
Collector-Emitter Voltage	V _{CEO}	45	V
Emitter-Base Voltage	V _{EBO}	6	V
Collector Current	Ic	100	mA

Thermal Characteristics – Total Device (@T_A = +25°C unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5) Total Device	P_{D}	350	mW
Thermal Resistance, Junction to Ambient (Note 5)	$R_{ heta JA}$	357	°C/W
Operating and Storage Temperature Range	T_J , T_{STG}	-65 to +150	°C

Note: 5. For a device surface mounted on minimum recommended pad layout FR-4 PCB with single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.

Thermal Characteristics – Total Device

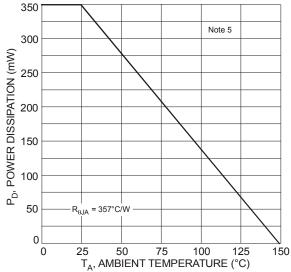


Figure 1 Power Dissipation vs. Ambient Temperature

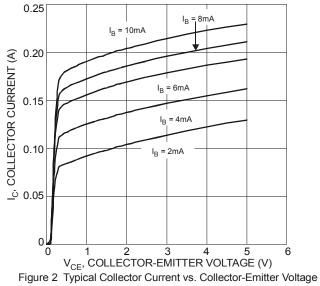


Electrical Characteristics (@T_A = +25°C unless otherwise specified.)

Characteristic (Note 6)	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	50	_	_	V	$I_C = 100 \mu A, I_B = 0$
Collector-Emitter Breakdown Voltage	BV _{CEO}	45	_	_	V	I _C = 10mA, I _B = 0
Emitter-Base Breakdown Voltage	BV _{EBO}	6	_	_	V	$I_E = 100\mu A, I_C = 0$
DC Current Gain	h _{FE}	420	650	800	_	V _{CE} = 5.0V, I _C = 2.0mA
Collector-Emitter Saturation Voltage	V _{CE(sat)}	-	55 130	250 600	mV	$I_C = 10$ mA, $I_B = 0.5$ mA $I_C = 100$ mA, $I_B = 5.0$ mA
Base-Emitter Saturation Voltage	V _{BE(sat)}		700 900	_	mV	$I_C = 10$ mA, $I_B = 0.5$ mA $I_C = 100$ mA, $I_B = 5.0$ mA
Base-Emitter Voltage	V _{BE(on)}	580 —	660 —	700 770	mV	$V_{CE} = 5.0V, I_{C} = 2.0mA$ $V_{CE} = 5.0V, I_{C} = 10mA$
Collector-Cutoff Current	I _{CES}	_	_	15	nA	V _{CE} = 50V
Collector-Cutoff Current	I _{CBO}	_	_	15 5	nΑ μΑ	V _{CB} = 30V V _{CB} = 30V, T _A = +150°C
Gain Bandwidth Product	f _T	100	_	_	MHz	V _{CE} = 5.0V, I _C = 10mA, f = 100MHz
Collector-Base Capacitance	C _{CBO}	_	2.0	_	pF	V _{CB} = 10V, f = 1.0MHz

Note:

6. Measured under pulsed conditions. Pulse width $\leq 300 \mu s.$ Duty cycle $\leq~2\%.$



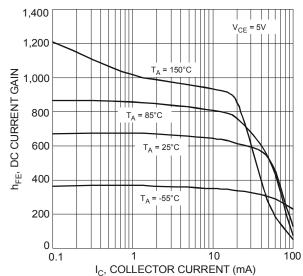


Figure 3 Typical DC Current Gain vs. Collector Current



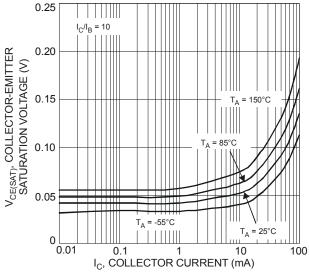
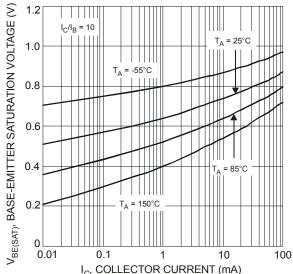


Figure 4 Typical Collector-Emitter Saturation Voltage vs. Collector Current



I_C, COLLECTOR CURRENT (mA)
Figure 6 Typical Base-Emitter Saturation Voltage
vs. Collector Current

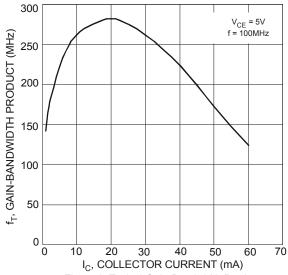


Figure 8 Typical Gain-Bandwidth Product vs. Collector Current

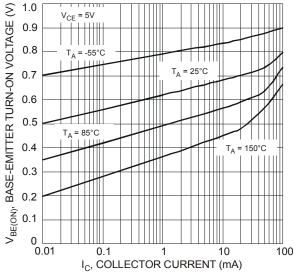


Figure 5 Typical Base-Emitter Turn-On Voltage vs. Collector Current

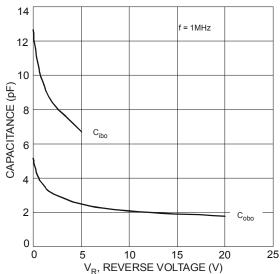
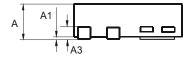


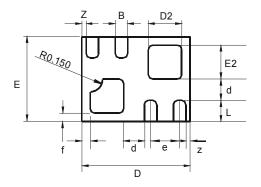
Figure 7 Typical Capacitance Characteristics



Package Outline Dimensions

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.

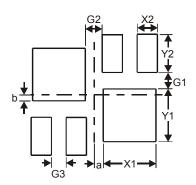




X2-DFN1310-6				
Dim	Min	Max	Тур	
Α		0.40	_	
A1	0	0.05	0.02	
A3	_	_	0.13	
b	0.10	0.20	0.15	
D	1.25	1.38	1.30	
d	_	_	0.25	
D2	0.30	0.50	0.40	
Е	0.95	1.075	1.00	
е	_	_	0.35	
E2	0.30	0.50	0.40	
f			0.10	
L	0.20	0.30	0.25	
Z	_	_	0.05	
All Dimensions in mm				

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
G1	0.16
G2	0.17
G3	0.15
X1	0.52
X2	0.20
Y1	0.52
Y2	0.375
а	0.09
h	0.06



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